L Number	Hits	Search Text	DB	Time stamp
-	400502		USPAT;	2004/08/22 12:15
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	002024		IBM_TDB USPAT:	2004/08/22 12:17
-	803924	oxygen or "o.sub.2" or "o.sub2." or "o2"	USPAT; US-PGPUB;	2004/08/22 12:1/
			EPO; JPO;	
			DERWENT;	
1			IBM TDB	
-	1104427	hydrogen or "h.sub.2" or "h.sub2." or "h2"	USPĀT;	2004/08/22 12:18
			US-PGPUB;	
1			EPO; JPO;	
]			DERWENT; IBM TDB	
_	796149	nitrogen or "n.sub.2" or "n.sub2." or "n2"	USPAT;	2004/08/22 12:18
	,30143	Interogen of n.sub.2 of n.sub2. of n2	US-PGPUB;	20047,007,22 12.10
			EPO; JPO;	
			DERWENT;	l
			IBM_TDB	
_	1875166		USPAT;	2004/08/22 12:19
		or (hydrogen or "h.sub.2" or "h.sub2." or	US-PGPUB;	
		"h2") or (nitrogen or "n.sub.2" or "n.sub2." or "n2")	EPO; JPO; DERWENT;	
		m.subz. or mz-)	IBM TDB	
_	3645038	treat\$5 or anneal\$5 or expos\$5	USPAT;	2004/08/22 12:21
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	31912	<del>-</del>	USPAT;	2004/08/22 12:21
		expos\$5) same ((oxygen or "o.sub.2" or "o.sub2." or "o2") or (hydrogen or	US-PGPUB; EPO; JPO;	4
1		"h.sub.2" or "h.sub2." or "h2") or	DERWENT;	
		(nitrogen or "n.sub.2" or "n.sub2." or	IBM TDB	
		"n2"))		
-	880783	gate	USPAT;	2004/08/22 14:54
			US-PGPUB;	
			EPO; JPO;	ļ
			DERWENT; IBM TDB	
_	33767	ldd or light\$3 adj3 dop\$3	USPAT;	2004/08/22 12:23
	] 33,0,	land of figure and adopt a	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
-	2422	(plasma same (treat\$5 or anneal\$5 or	USPAT;	2004/08/22 12:29
		expos\$5) same ((oxygen or "o.sub.2" or "o.sub2." or "o2") or (hydrogen or	US-PGPUB; EPO; JPO;	
		"h.sub.2" or "h.sub2." or "h2") or	DERWENT;	
1		(nitrogen or "n.sub.2" or "n.sub2." or	IBM TDB	
		"n2"))) and gate and (ldd or light\$3 adj3		
		dop\$3)		
-	44119	plasma near5 ((oxygen or "o.sub.2" or	USPAT;	2004/08/22 16:00
		"o.sub2." or "o2") or (hydrogen or	US-PGPUB;	
		"h.sub.2" or "h.sub2." or "h2") or   (nitrogen or "n.sub.2" or "n.sub2." or	EPO; JPO; DERWENT;	
[		nitrogen or "n.sub.2" or "n.sub2." or "n.sub2."	IBM TDB	
_	71247	plasma near10 (treat\$5 or anneal\$5 or	USPAT;	2004/08/22 12:30
		expos\$5)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/00/00 10 55
-	14574	(plasma near5 ((oxygen or "o.sub.2" or	USPAT;	2004/08/22 12:30
		"o.sub2." or "o2") or (hydrogen or "h.sub.2" or "h.sub2." or "h2") or	US-PGPUB; EPO; JPO;	
		(nitrogen or "n.sub.2" or "n.sub2." or	DERWENT;	
		"n2"))) same (plasma near10 (treat\$5 or	IBM TDB	
		anneal\$5 or expos\$5))		

		<del></del>	<del>,</del>	
-	841	((plasma near5 ((oxygen or "o.sub.2" or	USPAT;	2004/08/22 12:31
		"o.sub2." or "o2") or (hydrogen or	US-PGPUB;	
		"h.sub.2" or "h.sub2." or "h2") or	EPO; JPO;	
		(nitrogen or "n.sub.2" or "n.sub2." or	DERWENT;	
		"n2"))) same (plasma near10 (treat\$5 or	IBM_TDB	
		anneal\$5 or expos\$5))) and gate and (ldd		
		or light\$3 adj3 dop\$3)		
-	555217		USPAT;	2004/08/22 12:33
		field adj5 transistor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2802509	drain or source	USPĀT;	2004/08/22 12:34
			US-PGPUB;	
			EPO; JPO;	1
			DERWENT;	
			IBM TDB	
_	839	(((plasma near5 ((oxygen or "o.sub.2" or	USPAT;	2004/08/22 12:35
		"o.sub2." or "o2") or (hydrogen or	US-PGPUB;	
		"h.sub.2" or "h.sub2." or "h2") or	EPO; JPO;	
		(nitrogen or "n.sub.2" or "n.sub2." or	DERWENT;	
		"n2"))) same (plasma near10 (treat\$5 or	IBM TDB	
		anneal\$5 or expos\$5))) and gate and (ldd		
		or light\$3 adj3 dop\$3)) and ((mosfet or		
		mos or fet or misfet or igfet or field		
		adj5 transistor) or (drain or source))		
_	280306		USPAT;	2004/08/22 12:37
	200300	Implante	US-PGPUB;	2001,00,22 12.0.
			EPO; JPO;	
		·	DERWENT;	
			IBM TDB	
	656	((((plasma near5 ((oxygen or "o.sub.2" or	USPAT;	2004/08/22 12:37
	656	"o.sub2." or "o2") or (hydrogen or	US-PGPUB;	2004/00/22 12:3/
		"h.sub.2" or "h.sub2." or "h2") or	EPO; JPO;	
		(nitrogen or "n.sub.2" or "n.sub2." or	DERWENT;	
	i	"n2"))) same (plasma near10 (treat\$5 or	IBM TDB	
		anneal\$5 or expos\$5))) and gate and (ldd	154-155	
		or light\$3 adj3 dop\$3)) and ((mosfet or		
		mos or fet or misfet or igfet or field		
		adj5 transistor) or (drain or source)))		
		and implant\$6		
-	213935		USPAT;	2004/08/22 12:37
	220000		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
1 -	53	(((((plasma near5 ((oxygen or "o.sub.2" or	USPĀT;	2004/08/22 13:01
1	33	"o.sub2." or "o2") or (hydrogen or	US-PGPUB;	
		"h.sub.2" or "h.sub2." or "h2") or	EPO; JPO;	
		(nitrogen or "n.sub.2" or "n.sub2." or	DERWENT;	
		"n2"))) same (plasma near10 (treat\$5 or	IBM TDB	
		anneal\$5 or expos\$5))) and gate and (ldd	1511-100	
		or light\$3 adj3 dop\$3)) and ((mosfet or		
		mos or fet or misfet or igfet or field		
		adj5 transistor) or (drain or source)))		
l _	624666	and implant\$6) and pocket (mosfet or mos or fet or misfet or igfet	USPAT;	2004/08/22 16:08
-	024000		US-PGPUB;	2007/00/22 10:00
		or field adj5 transistor) or pmos or nmos	1	
		or cmos	EPO; JPO;	
			DERWENT;	
I _	2544	(otabéd or pattornéd) poseso gato poseso	IBM_TDB USPAT;	2004/08/22 13:04
-	2544	1 ' '		2004/00/22 13:04
	1	damag\$4	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
L	L		IBM_TDB	L

253					
anneal\$5 or expos\$5) same ((oxygen or "0.sub.2." or "0.sub.2." or "0.sub.2." or "0.sub.2." or "0.sub.2." or "0.sub.2." or "1.sub.2." or polycrystal\$4) adj2 (si or silicon)   Same (plasma near5 ((oxygen or "0.sub.2." or "0.su	-	253			2004/08/22 14:52
- 0.5ub.2" or "0.5ub.2." or "0.5ub.2" or "h.sub.2." or "h.sub.2." or "h.sub.2." or "h.sub.2." or "h.sub.2." or "h.sub.2." or "n.sub.2." or polyerystal84) adj2 (si or silicon)   Sump (plasma near5 (coxygen or "0.5ub.2" or "0.5ub.2" or "n.sub.2." or "n.sub				1	
(hydrogen or "h.sub.2" or "h.sub.2" or "h.sub.2" or "n.sub2." or "n.sub2." or "n.sub.2" or polysricon or polysion or (poly or polycrystal84) adj2 (si or silicon)   Sept. PGPUB; EPG, JPG, DERWENT; IBM TDB		İ			
- 83650 - 945231 - 945231 - 945231 - 945231 - 945231 - 310 - passivat\$5 - 310 - 310 - passivat\$5 same (gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon) - 310 - passivat\$5 same (gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon) - 310 - 31	ľ			IBM TDB	
- 945231 gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon)				_	
945231 gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon)  - 310 passivat\$5 same (gate or polysilicon or polysi or (poly or or silicon)) same (plasma near\$ ((oxygen or "o.sub.2" or "n.sub2." or "n.su					
Passivat\$5 same (gate or polysilicon or or onsub.2" or or onsub.2 or onsub	-	63650		USPAT;	2004/08/22 14:52
- 945231 gate or polysilicon or polysi or (poly or polycrystal84) adj2 (si or silicon)  - 310 passivat\$5 same (gate or polysilicon or polysi or (poly or polycrystal84) adj2 (si or silicon)				US-PGPUB;	
345231   gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon)   SPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; USPA				EPO; JPO;	
945231 gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon)  - 310 passivat\$5 same (gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon)  - 310 passivat\$5 same (gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon) same (plasma near\$ (loxygen or "o.sub.2" or "o.sub.2" or "o.sub.2" or "h.sub.2" or "h.sub.2" or "h.sub.2" or "h.sub.2" or "n.sub.2" or "n.sub.2" or "n.sub.2" or "n.sub.2" or "n.sub.2" or "n.sub.2" or "o.sub.2" or "o.sub.2" or "o.sub.2" or "o.sub.2" or "o.sub.2" or "o.sub.2" or "n.sub.2" or "o.sub.2" or "n.sub.2"		İ		DERWENT;	
Dolycrystal\$4) adj2 (si or silicon)		İ			
310	-	945231		I	2004/08/22 14:56
- 310 passivat\$5 same (gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon) ) same (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "			polycrystal\$4) adj2 (si or silicon)	1	
Desirate   Same (gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon)   same (plasma near5 (loxygen or "o.sub.2" or "o.sub.2" or "n.sub.2" or "h.sub.2" or "n.sub.2"  or "n.sub.2." or "n.sub.2.		!			
310   passivat\$S same (gate or polysilicon or polysi or (poly) or polycrystal\$4) adj2 (si or silicon)   same (plasma near\$5 ((oxygen or "o.sub.2" or "n.sub2." or "h.sub2."					
Dolysi or (poly or polycrystal94) adj2 (si or silicon) ) same (plasma nears (oxygen to "h.sub.2" or "o.sub2." or "o.sub2." or "o.sub2." or "o.sub2." or "o.sub2." or "o.sub2." or "o.sub2." or "o.sub2." or "o.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "o.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "o.sub2."					0001/00/00 11 50
or silicon)   same (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o.sub2." or "o.sub2." or "o.sub2." or "o.sub2." or "o.sub2." or "o.sub2." or "o.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "o.sub2." or or "o.sub2." or or "o.sub2." or or "o.sub2." or or "o.sub2." or or or or or o.sub2." or or or or or or or or or or or or or	-	310		1	2004/08/22 14:58
or "o. sub.2." or "o. sub2." or "o.2") or (hydrogen of "h. sub.2." or "h. sub2." or "h. sub2." or "n					
(hydrogen of "h.sub.2" or "h.sub2." or "n2") or (nitrogen or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n2"))  191 (passivat\$5 same (glate or polysilicon or polysil or silicon)) same (plasma near5 ((oxygen or "n.sub.2" or "n.sub2." or "n2")) or (hydrogen or "h.sub.2" or "n.sub2." or "n2")) or (hydrogen or "n.sub.2" or "n.sub2." or "n2"))) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor) or pmos or nmos or cmos)  - 4563 438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "n.sub2." or "n					•
""" (nitrogen or "n.sub.2" or "n.sub.2" or "n.sub.2" or "n.sub2." or "n.sub2." or polysi. or (poly or polycrystais4) adj2 (si or silicon) ) same (plasma near5 ((oxygen or "o.sub2." or "o.sub2." or "n.sub2." or "n.		İ			
"In. sub2." or "n2"))   (passivat\$5 same (gate or polysilicon or polysi. or (poly or polycrystal\$4) adj2 (si or silicon) ) same (plasma near5 ((oxygen or "o. sub2." or "o. sub2." or "h. sub2." or "h. sub2." or "h. sub2." or "n2"))) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor) or pmos or mmos or cmos)   438/585.ccls. or 438/595.ccls. or 438/798   or 438/303.ccls. or 438/305.ccls. or 438/798   or 438/303.ccls. or hydrogen or "o. sub2." or "o. sub2." or "o. sub2." or "n				T DIM T T DB	
191					
Dolysi or (poly or polycrystal\$4) adj2 (si or silicon)   same (plasma near5 ((oxygen or "0.sub.2" or "0.sub2." or "0.sub	l _	101		IISPAT.	2004/08/22 15:55
or silicon) same (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o.sub2." or "o.sub2." or "o.sub2." or "h.sub.2" or "h.sub.2" or "n.sub2." or "n.sub.2" or "n.sub.2" or mos or fet or misfet or igfet or field adj5 transistor) or pmos or nmos or cmos) or 438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "n.sub2." or "n.sub		191		1	2004/00/22 13:33
or "o. sub.2" or "o. sub.2." or "o2") or "h. sub.2" or "h. sub.2" or "h. sub.2" or "h. sub.2" or "n. sub.2" or "n. sub.2" or "n. sub.2." or "n. sub.2." or "n. sub.2." or "n. sub.2." or "n. sub.2." or "n. sub.2." or fet or misfet or igfet or field adj5 transistor) or pmos or nmos or cmos)  4563 438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o. sub.2" or "n. sub.2.					
(hydrogen or "h.sub.2" or "h.sub2." or "h2") or (nitrogen or "n.sub.2" or "n.sub.2" or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or misfet or igfet or field adj5 transistor) or pmos or nmos or cmos)  4363 438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls. USPAT; USPGPUB; EPC, JPC; DERRENT; IBM TDB (plasma near5 ((oxygen or "o.sub.2" or "n.sub.2" or "n.sub.2" or "n.sub2." or					
"h2") or (nitrogen or "n.sub.2" or "n.sub2." or "nsub2." or "n2"))) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor) or pmos or nmos or cmos)  4563 438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.  - 4563 438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.  - 554 (438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "h.sub2." or "n.sub2." or "				1	
"n.sub2." or "n2"))) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor) or pmos or nmos or cmos) 438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.  - 4563 (438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.  - 554 (438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub2" or "h.sub2." or "h.sub2." or "n2") or (hydrogen or "n.sub2." or "n2")))  - 459 ((438/585.ccls. or 438/595.ccls. or 438/798 or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub2." or "n.sub2." or "					
or fet or misfet or igfet or field adj5 transistor) or pmos or nmos or cmos) 438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.  -			"n.sub2." or "n2")))) and ((mosfet or mos		
- 4563 438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.  - 554 (438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "n.sub2." or "n					
Or 438/303.ccls. or 438/305.ccls.   US-PGPUB; EPG, JPO; DERWENT; IBM_TDB   US-PAT; US-PGPUB; EPG, JPO; DERWENT; IBM_TDB   US-PAT; US-PGPUB; EPG, JPO; DERWENT; IBM_TDB   US-PAT; US-PGPUB; EPG, JPO; DERWENT; IBM_TDB   US-PAT; US-PGPUB; EPG, JPO; DERWENT; IBM_TDB   US-PAT; US-PGPUB; EPG, JPO; DERWENT; IBM_TDB   US-PAT; US-PGPUB; EPG, JPO; DERWENT; IBM_TDB   US-PAT; US-PGPUB; EPG, JPO; DERWENT; IBM_TDB   US-PAT; US-PGPUB; EPG, JPO; DERWENT; IBM_TDB   US-PAT; US-PGPUB; EPG, JPO; DERWENT; IBM_TDB   US-PGPUB; EPG, JPO; JPO; DERWENT; IBM_TDB   US-PGPUB; EPG, JPO; JPO; DERWENT; IBM_TDB   US-PGPUB; EPG, JPO; JPO; DERWENT; IBM_TDB   US-PGPUB; EPG, JPO; JPO; JPO; JPO; JPO; JPO; JPO; JPO;					
- 554 (438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "h.sub.2" or "h.sub.2" or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "o.sub2." or "o.sub2." or "n.sub2."	-	4563		USPAT;	2004/08/22 16:00
DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB			or 438/303.ccls. or 438/305.ccls.	US-PGPUB;	
- 554 (438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub2." or "h.sub2." or "h.sub2." or "n.sub2."				1	
-					
or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "h.sub2." or "h.sub2." or "h.sub2." or "n.sub2." or "o.sub2." or "o.sub2." or "o.sub2." or "o.sub2." or "o.sub2." or "o.sub2." or "n.sub2." or "n.su			420/505		2004/00/00 16 00
(plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o2") or (hydrogen or "h.sub.2" or "h.sub2." or "n2")) or (nitrogen or "n.sub2." or "n.sub2." or "n.sub2." or "n2")))  459 ((438/585.ccls. or 438/595.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "h.sub.2" or "h.sub.2" or "h.sub2." or "h.sub.2" or "n.sub2."	-	554		•	2004/08/22 16:02
"o.sub2." or "o2") or (hydrogen or "h.sub.2" or "h.sub2." or "h2") or (nitrogen or "n.sub2." or "n.sub2." or "n2")))  459 ((438/585.ccls. or 438/595.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n2")))) and (gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon) ) and (drain or source)  438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "d38/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o.sub2." or "n.sub2."				1	
"h.sub.2" or "h.sub2." or "h2") or (nitrogen or "n.sub.2" or "n.sub2." or "n2")))  (459 ((438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o2") or (hydrogen or "h.sub.2" or "h.sub2." or "n2")))) and (gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon) ) and (drain or source) ((438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/798 or 438/303.ccls. or 438/798 or 438/303.ccls. or 438/798 or 438/303.ccls. or (nitrogen or "n.sub2." or "o.sub.2" or "n.sub.2" or "h.sub2." or "n.sub2." or "n.sub.2" or "n.sub2." or "n.sub.2" or "n.sub2." or "n.sub.2" or "n.sub2." or "n.sub.2" or "n.sub2." or "n.sub.2" or "n.sub2." or "n2")))) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor)				i	
(nitrogen or "n.sub.2" or "n.sub2." or "n2"))  ((438/585.ccls. or 438/595.ccls. or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "h.sub.2" or "h.sub2." or "nsub2." or "n2"))) and (gate or polysilcon or polysi or (poly or polycrystal\$4) adj2 (si or silicon) ) and (drain or source)  ((438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o.sub2." or "o.sub2." or "o.sub2." or "n.sub.2" or "n.sub.2" or "n.sub.2" or "nsub.2"					
- 459 (438/585.ccls. or 438/595.ccls. or 438/305.ccls.) (438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "h.sub2." or "h.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n2")))) and (gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon) ) and (drain or source) ((438/585.ccls. or 438/595.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or (nitrogen or "n.sub2." or "h.sub2." or "n2")))) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor)				1 100	
- 459 ((438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.)  438/798 or 438/303.ccls. or 438/305.ccls.)  and (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "h.sub2." or "h.sub2." or "nasub2." or polysi or (poly or polycrystal\$4) adj2 (si or silicon) ) and (drain or source)  ((438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.)  and (plasma near5 ((oxygen or "o.sub2." or "o.sub2." or "o.sub2." or "o.sub2." or "nasub2." or "h.sub2." or "h.sub2." or "h.sub2." or "h.sub2." or "nasub2."					
438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub.2." or "o.sub2." or "h.sub.2" or "h.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "o.sub2." or "o.sub2." or polysi or (poly or polycrystal\$4) adj2 (si or silicon) and (drain or source)    438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o.sub2." or "o.sub2." or "o.sub2." or "o.sub2." or "h.sub2." or "h.sub2." or "h.sub2." or "n.sub2."	-	459		USPAT;	2004/08/22 16:03
and (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o.sub2." or "o.sub2." or (hydrogen or "h.sub.2" or "h.sub2." or "n.sub2." or "n2")))) and (gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon)) and (drain or source)  ((438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o.sub2." or "h.sub2." or "h.sub2." or "h.sub2." or "h.sub2." or "n2")))) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor)		1		1	
"h.sub.2" or "h.sub2." or "h2") or (nitrogen or "n.sub.2" or "n.sub2." or "n2")))) and (gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon)) and (drain or source)  ((438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o2") or (hydrogen or "h.sub.2" or "h.sub2." or "h.sub.2" or "n.sub2." or (nitrogen or "n.sub.2" or "n2")))) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor)				EPO; JPO;	
<pre>(nitrogen or "n.sub.2" or "n.sub2." or "n2")))) and (gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon) ) and (drain or source)  ((438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o2") or (hydrogen or "h.sub.2" or "h.sub2." or "h2") or (nitrogen or "n.sub2." or "n2")))) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor)</pre> USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB					
"n2")))) and (gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon) ) and (drain or source)  ((438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o.sub2." or "no.sub2." or "h.sub.2" or "h.sub2." or "h.sub2." or "nl.sub2." or "nl.su		j		IBM_TDB	
polysi or (poly or polycrystal\$4) adj2 (si or silicon) ) and (drain or source)  ((438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o.sub2." or "nh.sub.2" or "h.sub2." or "h.sub2." or "nh.sub2." or "nl.sub2." or		1			
or silicon) ) and (drain or source)  ((438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o.sub2." or "h.sub.2" or "h.sub2." or "h2") or (nitrogen or "n.sub2." or "n.sub2." or "n2")))) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor)					
- 390 ((438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub.2" or "o.sub.2" or "nh.sub.2" or "n			1		
438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub.2" or "o.sub.2" or "h.sub.2" or "h.sub.2" or "h.sub.2" or "h.sub.2" or "n.sub.2" or "n.sub.2" or "n.sub.2" or "n.sub.2" or "n.sub.2" or "n.sub.2" or misfet or igfet or field adj5 transistor)		222		Habba	2004/00/00 16 00
and (plasma near5 ((oxygen or "o.sub.2" or "o.sub.2" or "o.sub2." or (hydrogen or "h.sub.2" or "h.sub2." or "h.sub2." or "n.sub2." or "n.sub2." or "n.sub2." or "n2")))) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor)	-	390		1	2004/08/22 16:09
"o.sub2." or "o2") or (hydrogen or DERWENT; "h.sub.2" or "h.sub2." or "h2") or (nitrogen or "n.sub.2" or "n.sub2." or "n2")))) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor)		-			
"h.sub.2" or "h.sub2." or "h2") or (nitrogen or "n.sub.2" or "n.sub2." or "n2")))) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor)					
<pre>(nitrogen or "n.sub.2" or "n.sub2." or "n2")))) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor)</pre>				l .	
"n2")))) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor)				125-100	
misfet or igfet or field adj5 transistor)					

-	369	(((438/585.ccls. or 438/595.ccls. or	USPAT;	2004/08/22	16:11
1	1	438/798 or 438/303.ccls. or 438/305.ccls.)	US-PGPUB;		
	]	and (plasma near5 ((oxygen or "o.sub.2" or	EPO; JPO;		
1	İ	"o.sub2." or "o2") or (hydrogen or	DERWENT;		
	•	"h.sub.2" or "h.sub2." or "h2") or	IBM_TDB		
İ		(nitrogen or "n.sub.2" or "n.sub2." or	_		
İ		"n2")))) and ((mosfet or mos or fet or			
		misfet or igfet or field adj5 transistor)			
		or pmos or nmos or cmos)) and (drain or			
		source)			_

L Number	Hits	Search Text	DB	Time stamp
-	11144	ldd	USPAT;	2004/08/25 10:02
_	139757	pocket	US-PGPUB USPAT; US-PGPUB	2004/08/23 11:29
-	10956	punchthrough or punch adj2 through	USPAT; US-PGPUB	2004/08/23 11:29
_	262	pocket with (punchthrough or punch adj2 through)	USPAT; US-PGPUB	2004/08/23 11:29
-	150	ldd and (pocket with (punchthrough or punch adj2 through))	USPAT; US-PGPUB	2004/08/23 15:52
-	122736	anneal\$4	USPAT; US-PGPUB	2004/08/23 15:52
-	150	ldd and (pocket with (punchthrough or punch adj2 through))	USPAT; US-PGPUB	2004/08/23 15:52
-	76	anneal\$4 and (ldd and (pocket with (punchthrough or punch adj2 through)))	USPAT; US-PGPUB	2004/08/23 16:27
-	3395	(pocket or halo) with implant\$5	USPAT; US-PGPUB	2004/08/23 16:28
_	697715	interconnect\$5 or wiring	USPAT; US-PGPUB	2004/08/23 16:29
-	11144	ldd	USPAT; US-PGPUB	2004/08/23 16:29
-	14669	ldd or light\$3 adj5 drain	USPAT; US-PGPUB	2004/08/23 16:29
-	206	((pocket or halo) with implant\$5) and (interconnect\$5 or wiring) and (1dd or light\$3 adj5 drain) and anneal\$4	USPAT; US-PGPUB	2004/08/23 16:30
_	1105431	hydrogen or "h2" or "h.sub.2" or "h.sub2."	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/08/25 10:05
-	1828622	plasma or discharg\$3	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/08/25 10:04
-	23926	(hydrogen or "h2" or "h.sub.2" or "h.sub2.") near5 (plasma or discharg\$3)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/08/25 10:06
_	1437627	damag\$4 or defect	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/08/25 10:06
-	1786934	etch\$4 or pattern\$4	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/08/25 10:06
-	158349	polysi or polysilicon or (polycrystal\$4 or poly) adj2 (si or silicon)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/08/25 10:07
-	1545	(damag\$4 or defect) with (etch\$4 or pattern\$4) with (polysi or polysilicon or (polycrystal\$4 or poly) adj2 (si or silicon))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/08/25 10:08
-	2	((hydrogen or "h2" or "h.sub.2" or "h.sub2.") near5 (plasma or discharg\$3)) same ((damag\$4 or defect) with (etch\$4 or pattern\$4) with (polysi or polysilicon or (polycrystal\$4 or poly) adj2 (si or silicon)))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 10:10

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<u> </u>	53776	(damag\$4 or defect) with (etch\$4 or	USPAT;	2004/08/25 10:10
	357,75	pattern\$4)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	İ
_	187	((hydrogen or "h2" or "h.sub.2" or	USPAT;	2004/08/25 10:13
	107	"h.sub2.") near5 (plasma or discharg\$3))	US-PGPUB;	2004/00/23 10:13
		same ((damag\$4 or defect) with (etch\$4 or	EPO; JPO;	
		pattern\$4))	DERWENT;	
		paccerny4//	IBM TDB	
	881572	l anto	USPAT;	2004/08/25 10:13
_	0013/2	gate	US-PGPUB;	2004/00/25 10.15
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	78	(((hydrogen or "h2" or "h.sub.2" or	USPAT;	2004/08/25 10:14
_		"h.sub2.") near5 (plasma or discharg\$3))	US-PGPUB;	2004/00/25 10:14
ļ .		same ((damag\$4 or defect) with (etch\$4 or	EPO; JPO;	
		pattern\$4))) and gate	DERWENT;	
		Paccern94/// and gate	IBM TDB	
	85621	   (etch\$4 or pattern\$4) with gate	USPAT;	2004/08/25 10:15
-	65621	(econya or paccernya) with gate	US-PGPUB;	2004/00/23 10:13
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	46	///hudragen on !!h?!! on !!h gub ?!!	USPAT:	2004/08/25 10:44
-	46	1 ( ( ( - 2 2	US-PGPUB;	2004/00/25 10:44
		"h.sub2.") near5 (plasma or discharg\$3))	EPO; JPO;	
		same ((damag\$4 or defect) with (etch\$4 or		
		pattern\$4))) and ((etch\$4 or pattern\$4)	DERWENT;	
		with gate)	IBM_TDB	2004/08/25 10:44
_	2	("5350710").PN.	USPAT;	2004/08/25 10:44
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
L			IBM_TDB	<u> </u>

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